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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

66MHz
CANbus, I ² C, LINbus, SPI, SSC, UART/USART, USI
I ² S, POR, PWM, WDT
48
160KB (160K x 8)
FLASH
-
10K x 8
3V ~ 5.5V
A/D 19x12b
Internal
-40°C ~ 125°C (TA)
Surface Mount
64-LQFP Exposed Pad
PG-LQFP-64-22



16/32-Bit

Architecture

XC2230L, XC2234L

16/32-Bit Single-Chip Microcontroller with 32-Bit Performance XC2000 Family / Econo Line

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Microcontrollers



Summary of Features

- On-Chip Peripheral Modules
 - Synchronizable 12-bit A/D Converter with up to 19 channels, conversion time below 1 μ s, optional data preprocessing (data reduction, range check), broken wire detection
 - 16-channel general purpose capture/compare unit (CC2)
 - Two capture/compare units for flexible PWM signal generation (CCU6x)
 - Multi-functional general purpose timer unit with 5 timers
 - Up to 4 serial interface channels to be used as UART, LIN, high-speed synchronous channel (SPI/QSPI), IIC bus interface (10-bit addressing, 400 kbit/s), IIS interface
 - On-chip MultiCAN interface (Rev. 2.0B active) with up to 32 message objects (Full CAN/Basic CAN) on 2 CAN nodes and gateway functionality
 - On-chip system timer and on-chip real time clock
- Single power supply from 3.0 V to 5.5 V
- Power reduction and wake-up modes with flexible power management
- Programmable window watchdog timer and oscillator watchdog
- Up to 48 general purpose I/O lines
- · On-chip bootstrap loaders
- Supported by a full range of development tools including C compilers, macroassembler packages, emulators, evaluation boards, HLL debuggers, simulators, logic analyzer disassemblers, programming boards
- On-chip debug support via Device Access Port (DAP), Single-Pin DAP (SPD) or JTAG interface
- 64-pin Green LQFP package, 0.5 mm (19.7 mil) pitch

Ordering Information

The ordering code for an Infineon microcontroller provides an exact reference to a specific product. This ordering code identifies:

- the function set of the corresponding product type
- the temperature range¹⁾:
 - SAF-...: -40°C to 85°C
 - SAH-...: -40°C to 110°C
 - SAK-...: -40°C to 125°C
- the package and the type of delivery.

For ordering codes for the XC223[04]L please contact your sales representative or local distributor.

This document describes several derivatives of the XC223[04]L group:

Basic Device Types are readily available and Special Device Types are only available on request.

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¹⁾ Not all derivatives are offered in all temperature ranges.



General Device Information

 Table 6
 Pin Definitions and Functions (cont'd)

Pin	Symbol	Ctrl.	Туре	Function
38	P2.10	00 / 1	St/B	Bit 10 of Port 2, General Purpose Input/Output
38				, , , , , , , , , , , , , , , , , , , ,
	U0C1_DOUT	01	St/B	USIC0 Channel 1 Shift Data Output
	U0C0_SELO 3	O2	St/B	USIC0 Channel 0 Select/Control 3 Output
	CC2_CC23	O3 / I	St/B	CAPCOM2 CC23IO Capture Inp./ Compare Out.
	U0C1_DX0E	I	St/B	USIC0 Channel 1 Shift Data Input
	CAPINA	I	St/B	GPT12E Register CAPREL Capture Input
39	P2.11	O0 / I	St/B	Bit 11 of Port 2, General Purpose Input/Output
	U0C0_SELO 2	O1	St/B	USIC0 Channel 0 Select/Control 2 Output
	U0C1_SELO 2	O2	St/B	USIC0 Channel 1 Select/Control 2 Output
	U1C1_DX2A	I	St/B	USIC1 Channel 1 Shift Control Input
40	P2.12	O0 / I	St/B	Bit 12 of Port 2, General Purpose Input/Output
	U0C0_SELO 4	O1	St/B	USIC0 Channel 0 Select/Control 4 Output
	U0C1_SELO 3	O2	St/B	USIC0 Channel 1 Select/Control 3 Output
	U1C1_SCLK OUT	О3	St/B	USIC1 Channel 1 Shift Clock Output
	U1C1_DX1A	I	St/B	USIC1 Channel 1 Shift Clock Input
41,	P2.13	O0 / I	St/B	Bit 13 of Port 2, General Purpose Input/Output
	U1C1_DOUT	01	St/B	USIC1 Channel 1 Shift Data Output
	CCU63_COU T60	O2	St/B	CCU63 Channel 0 Output
	U1C1_DX0B	I	St/B	USIC1 Channel 1 Shift Data Input
	U1C0_DX0B	I	St/B	USIC1 Channel 0 Shift Data Input



Functional Description

With its maximum resolution of 2 system clock cycles, the **GPT2 module** provides precise event control and time measurement. It includes two timers (T5, T6) and a capture/reload register (CAPREL). Both timers can be clocked with an input clock which is derived from the CPU clock via a programmable prescaler or with external signals. The counting direction (up/down) for each timer can be programmed by software or altered dynamically with an external signal on a port pin (TxEUD). Concatenation of the timers is supported with the output toggle latch (T6OTL) of timer T6, which changes its state on each timer overflow/underflow.

The state of this latch may be used to clock timer T5, and/or it may be output on pin T6OUT. The overflows/underflows of timer T6 can also be used to clock the CAPCOM2 timers and to initiate a reload from the CAPREL register.

The CAPREL register can capture the contents of timer T5 based on an external signal transition on the corresponding port pin (CAPIN); timer T5 may optionally be cleared after the capture procedure. This allows the XC223[04]L to measure absolute time differences or to perform pulse multiplication without software overhead.

The capture trigger (timer T5 to CAPREL) can also be generated upon transitions of GPT1 timer T3 inputs T3IN and/or T3EUD. This is especially advantageous when T3 operates in Incremental Interface Mode.

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Functional Description

3.13 MultiCAN Module

The MultiCAN module contains two independently operating CAN nodes with Full-CAN functionality which are able to exchange Data and Remote Frames using a gateway function. Transmission and reception of CAN frames is handled in accordance with CAN specification V2.0 B (active). Each CAN node can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers.

The two CAN nodes share a common set of message objects. Each message object can be individually allocated to either of the CAN nodes. Besides serving as a storage container for incoming and outgoing frames, message objects can be combined to build gateways between the CAN nodes or to set up a FIFO buffer.

The message objects are organized in double-chained linked lists, where each CAN node has its own list of message objects. A CAN node stores frames only into message objects that are allocated to its own message object list and it transmits only messages belonging to this message object list. A powerful, command-driven list controller performs all message object list operations.

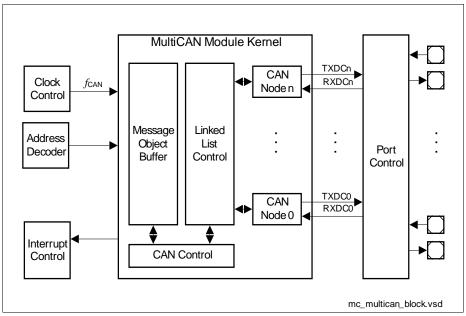


Figure 11 Block Diagram of MultiCAN Module



Electrical Parameters

8) Value is controlled by on-chip regulator.

4.2 Voltage Range definitions

The XC223[04]L timing depends on the supply voltage. If such a dependency exists the timing values are given for 2 voltage areas commonly used. The voltage areas are defined in the following tables.

Table 14 Upper Voltage Range Definition

Parameter	Symbol	Values		Unit	Note /	
		Min.	Тур.	Max.		Test Condition
Digital supply voltage for IO pads and voltage regulators	$V_{DDP}SR$	4.5	5.0	5.5	V	

Table 15 Lower Voltage Range Definition

Parameter	Symbol	Values		Values Unit		Note /
		Min.	Тур.	Max.		Test Condition
Digital supply voltage for IO pads and voltage regulators	$V_{DDP}SR$	3.0	3.3	4.5	V	

4.2.1 Parameter Interpretation

The parameters listed in the following include both the characteristics of the XC223[04]L and its demands on the system. To aid in correctly interpreting the parameters when evaluating them for a design, they are marked accordingly in the column "Symbol":

CC (Controller Characteristics):

The logic of the XC223[04]L provides signals with the specified characteristics.

SR (System Requirement):

The external system must provide signals with the specified characteristics to the XC223[04]L.



Electrical Parameters

4.3.2 DC Parameters for Lower Voltage Area

Keeping signal levels within the limits specified in this table ensures operation without overload conditions. For signal levels outside these specifications, also refer to the specification of the overload current $I_{\rm OV}$.

Note: Operating Conditions apply.

Table 17 is valid under the following conditions: $V_{\rm DDP}{\geq}~3.0~{\rm V};~V_{\rm DDP}{\rm typ.}~3.3~{\rm V};~V_{\rm DDP}{\leq}~4.5~{\rm V}$

Table 17 DC Characteristics for Lower Voltage Range

Parameter	Symbol		Values	3	Unit	Note /
		Min.	Тур.	Max.		Test Condition
Pin capacitance (digital inputs/outputs).	C _{IO} CC	_	-	10	pF	not subject to production test
Input Hysteresis ¹⁾	HYS CC	$0.07~\mathrm{x}$ V_DDP	_	_	V	R _S = 0 Ohm
Absolute input leakage current on pins of analog ports ²⁾	I _{OZ1} CC	_	10	200	nA	$\begin{array}{c} V_{\rm IN} \!\!> V_{\rm SS} \; ; \\ V_{\rm IN} \!\!< V_{\rm DDP} \end{array}$
Absolute input leakage current for all other pins. 2)3)	I _{OZ2} CC	-	0.2	2	μΑ	$T_{\rm J} {\leq} \ 110 \ ^{\circ}{\rm C};$ $V_{\rm IN} {>} \ V_{\rm SS} \ ;$ $V_{\rm IN} {<} \ V_{\rm DDP}$
		_	0.2	6	μΑ	$T_{ m J} \le$ 150 °C; $V_{ m IN} > V_{ m SS}$; $V_{ m IN} < V_{ m DDP}$
Pull Level Force Current ⁴⁾	$ I_{PLF} SR$	150		_	μА	$\begin{aligned} &V_{\text{IN}} \!\! \geq V_{\text{IHmin}} \\ &(pulldown_ena \\ &bled); \\ &V_{\text{IN}} \!\! \leq V_{\text{ILmax}} \\ &(pullup_enable \\ &d); \end{aligned}$
Pull Level Keep Current ⁵⁾	I _{PLK} SR	_	-	10	μА	$\begin{aligned} V_{\text{IN}} &\geq V_{\text{IHmin}} \\ (pullup_enable \\ d); \\ V_{\text{IN}} &\leq V_{\text{ILmax}} \\ (pulldown_enabled) \end{aligned}$



Electrical Parameters

Table 17 DC Characteristics for Lower Voltage Range (cont'd)

Parameter	Symbol		Unit	Note /		
		Min.	Тур.	Max.		Test Condition
Input high voltage (all except XTAL1)	$V_{IH}SR$	$0.7~\mathrm{x}$ V_DDP	-	V _{DDP} + 0.3	V	
Input low voltage (all except XTAL1)	$V_{IL}SR$	-0.3	_	0.3 x V_{DDP}	V	
Output High voltage ⁶⁾	$V_{OH}CC$	V _{DDP} - 1.0	-	_	٧	$I_{OH} \geq I_{OHmax}$
		V _{DDP} - 0.4	-	_	٧	$I_{\text{OH}} \ge I_{\text{OHnom}}^{7)}$
Output Low Voltage ⁶⁾	$V_{OL}CC$	-	_	0.4	V	$I_{\rm OL} \le I_{\rm OLnom}^{8)}$
		_	_	1.0	V	$I_{OL} \leq I_{OLmax}$

- Not subject to production test verified by design/characterization. Hysteresis is implemented to avoid metastable states and switching due to internal ground bounce. It cannot suppress switching due to external system noise under all conditions.
- 2) If the input voltage exceeds the respective supply voltage due to ground bouncing $(V_{\rm IN} < V_{\rm SS})$ or supply ripple $(V_{\rm IN} > V_{\rm DDP})$, a certain amount of current may flow through the protection diodes. This current adds to the leakage current. An additional error current $(I_{\rm INJ})$ will flow if an overload current flows through an adjacent pin. Please refer to the definition of the overload coupling factor $K_{\rm OV}$.
- 3) The given values are worst-case values. In production test, this leakage current is only tested at 125 °C; other values are ensured by correlation. For derating, please refer to the following descriptions: Leakage derating depending on temperature (T_J = junction temperature [°C]): I_{OZ} = 0.05 x e^(1.5 + 0.028 x TJ-) [μA]. For example, at a temperature of 95 °C the resulting leakage current is 3.2 μA. Leakage derating depending on voltage level (DV = V_{DDP} V_{PIN} [V]): I_{OZ} = I_{OZtempmax} (1.6 x DV) (μA]. This voltage derating formula is an approximation which applies for maximum temperature.
- 4) Drive the indicated minimum current through this pin to change the default pin level driven by the enabled pull device.
- 5) Limit the current through this pin to the indicated value so that the enabled pull device can keep the default pin level.
- 6) The maximum deliverable output current of a port driver depends on the selected output driver mode. This specification is not valid for outputs which are switched to open drain mode. In this case the respective output will float and the voltage is determined by the external circuit.
- As a rule, with decreasing output current the output levels approach the respective supply level (VOL->VSS, VOH->VDDP). However, only the levels for nominal output currents are verified.
- 8) As a rule, with decreasing output current the output levels approach the respective supply level (V_{OL}->V_{SS}, V_{OH}->V_{DDP}). However, only the levels for nominal output currents are verified.

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Electrical Parameters

4.3.3 Power Consumption

The power consumed by the XC223[04]L depends on several factors such as supply voltage, operating frequency, active circuits, and operating temperature. The power consumption specified here consists of two components:

- The switching current I_S depends on the device activity
- The leakage current I_{1K} depends on the device temperature

To determine the actual power consumption, always both components, switching current $I_{\rm S}$ and leakage current $I_{\rm LK}$ must be added:

$$I_{\text{DDP}} = I_{\text{S}} + I_{\text{LK}}.$$

Note: The power consumption values are not subject to production test. They are verified by design/characterization.

To determine the total power consumption for dimensioning the external power supply, also the pad driver currents must be considered.

The given power consumption parameters and their values refer to specific operating conditions:

Active mode:

Regular operation, i.e. peripherals are active, code execution out of Flash.

Stopover mode:

Crystal oscillator and PLL stopped, Flash switched off, clock in most parts of domain DMP_M stopped.

Note: The maximum values cover the complete specified operating range of all manufactured devices.

The typical values refer to average devices under typical conditions, such as nominal supply voltage, room temperature, application-oriented activity.

After a power reset, the decoupling capacitors for $V_{\rm DDIM}$ are charged with the maximum possible current.

For additional information, please refer to Section 5.2, Thermal Considerations.

Note: Operating Conditions apply.



Electrical Parameters

Table 18 Switching Power Consumption

Parameter	Symbol	Values		ymbol Values Unit		Unit	Note /
		Min.	Тур.	Max.		Test Condition	
Power supply current (active) with all peripherals active and EVVRs on	I _{SACT} CC	_	6 + 0.5 $x f_{SYS}^{1)}$	$8 + 0.75 x f_{\text{SYS}}^{1)}$	mA	power_mode= active; voltage_range= both ²⁾³⁾⁴⁾	
Power supply current in stopover mode, EVVRs on	I _{SSO} CC	-	0.7	2.0	mA	power_mode= stopover; voltage_range= both	

¹⁾ f_{SYS} in MHz

Active Mode Power Supply Current

The actual power supply current in active mode not only depends on the system frequency but also on the configuration of the XC223[04]L's subsystem.

Besides the power consumed by the device logic the power supply pins also provide the current that flows through the pin output drivers.

A small current is consumed because the drivers' input stages are switched.

²⁾ The pad supply voltage pins ($V_{\rm DDPB}$) provide the input current for the on-chip EVVRs and the current consumed by the pin output drivers. A small current is consumed because the drivers input stages are switched.

³⁾ Please consider the additional conditions described in section "Active Mode Power Supply Current".

⁴⁾ The pad supply voltage only has a minor influence on this parameter.

Electrical Parameters

Table 23 A/D Converter Computation Table

GLOBCTR.5-0 (DIVA)	A/D Converter Analog Clock f_{ADCI}	INPCRx.7-0 (STC)	Sample Time ¹⁾
000000 _B	$f_{ exttt{SYS}}$	00 _H	$t_{ADCI} \times 2$
000001 _B	$f_{\rm SYS}$ / 2	01 _H	$t_{ADCI} \times 3$
000010 _B	$f_{\rm SYS}$ / 3	02 _H	$t_{ADCI} \times 4$
:	$f_{\rm SYS}$ / (DIVA+1)	:	$t_{ADCI} \times (STC+2)$
111110 _B	f _{SYS} / 63	FE _H	$t_{ADCI} \times 256$
111111 _B	f _{SYS} / 64	FF _H	$t_{ADCI} \times 257$

¹⁾ The selected sample time is doubled if broken wire detection is active (due to the presampling phase).

Converter Timing Example A:

Assumptions: $f_{SYS} = 80 \text{ MHz}$ (i.e. $t_{SYS} = 12.5 \text{ ns}$), DIVA = 03_H , STC = 00_H

Analog clock $f_{ADCI} = f_{SYS} / 4 = 20 \text{ MHz}, i.e. t_{ADCI} = 50 \text{ ns}$

Sample time $t_S = t_{ADCI} \times 2 = 100 \text{ ns}$

Conversion 12-bit:

 $t_{\text{C12}} = 16 \times t_{\text{ADCI}} + 2 \times t_{\text{SYS}} = 16 \times 50 \text{ ns} + 2 \times 12.5 \text{ ns} = 0.825 \text{ }\mu\text{s}$

Conversion 10-bit:

 $t_{\text{C10}} = 12 \times t_{\text{ADCI}} + 2 \times t_{\text{SYS}} = 12 \times 50 \text{ ns} + 2 \times 12.5 \text{ ns} = 0.625 \text{ }\mu\text{s}$

Conversion 8-bit:

 $t_{\text{C8}} = 10 \times t_{\text{ADCI}} + 2 \times t_{\text{SYS}} = 10 \times 50 \text{ ns} + 2 \times 12.5 \text{ ns} = 0.525 \text{ }\mu\text{s}$

Converter Timing Example B:

Assumptions: $f_{SYS} = 66 \text{ MHz}$ (i.e. $t_{SYS} = 15.2 \text{ ns}$), DIVA = 03_H , STC = 00_H

Analog clock $f_{ADCI} = f_{SYS} / 4 = 16.5 \text{ MHz}$, i.e. $t_{ADCI} = 60.6 \text{ ns}$

Sample time $t_S = t_{ADCI} \times 2 = 121.2 \text{ ns}$

Conversion 12-bit:

 $t_{\text{C12}} = 16 \times t_{\text{ADCI}} + 2 \times t_{\text{SYS}} = 16 \times 60.6 \text{ ns} + 2 \times 15.2 \text{ ns} = 1.0 \text{ }\mu\text{s}$

Conversion 10-bit:

 $t_{\text{C10}} = 12 \times t_{\text{ADCI}} + 2 \times t_{\text{SYS}} = 12 \times 60.6 \text{ ns} + 2 \times 15.2 \text{ ns} = 0.758 \text{ }\mu\text{s}$



Electrical Parameters

4.6 Flash Memory Parameters

The XC223[04]L is delivered with all Flash sectors erased and with no protection installed.

The data retention time of the XC223[04]L's Flash memory (i.e. the time after which stored data can still be retrieved) depends on the number of times the Flash memory has been erased and programmed.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

Table 27 Flash Parameters

Parameter	Symbol		Value	s	Unit	Note /
		Min.	Тур.	Max.		Test Condition
Parallel Flash module	$N_{PP}SR$	-	_	2 ¹⁾		$N_{\text{FL_RD}} \le 1$
program/erase limit depending on Flash read activity		_	_	1 ²⁾		<i>N</i> _{FL_RD} > 1
Flash erase endurance for security pages	N _{SEC} SR	10	-	-	cycle s	t _{RET} ≥ 20 years
Flash wait states ³⁾	N _{WSFLASH} SR	1	_	-		f _{SYS} ≤ 8 MHz
		2	_	_		$f_{\rm SYS} \le 13~{\rm MHz}$
		3	_	_		$f_{\rm SYS} \le 17~{\rm MHz}$
		4	_	_		$f_{\rm SYS}$ > 17 MHz
Erase time per sector/page	t _{ER} CC	_	7 ⁴⁾	8.0	ms	
Programming time per page	t _{PR} CC	_	34)	3.5	ms	
Data retention time	$t_{RET}CC$	20	-	-	year s	$N_{\rm ER} \le$ 1,000 cycl es
Drain disturb limit	$N_{\mathrm{DD}}\mathrm{SR}$	32	-	-	cycle s	



Electrical Parameters

Table 27 Flash Parameters (cont'd)

Parameter	Symbol		Values			Note /
		Min.	Тур.	Max.		Test Condition
Number of erase cycles	N _{ER} SR	-	_	15000	cycle s	t _{RET} ≥ 5 years; Valid for up to 64 user selected sectors (data storage)
		_	_	1000	cycle s	t _{RET} ≥ 20 years

All Flash module(s) can be erased/programmed while code is executed and/or data is read from only one Flash
module or from PSRAM. The Flash module that delivers code/data can, of course, not be erased/programmed.

Access to the XC223[04]L Flash modules is controlled by the IMB. Built-in prefetch mechanisms optimize the performance for sequential access.

Flash access waitstates only affect non-sequential access. Due to prefetch mechanisms, the performance for sequential access (depending on the software structure) is only partially influenced by waitstates.

²⁾ Flash module 1 can be erased/programmed while code is executed and/or data is read from Flash module 0.

³⁾ Value of IMB IMBCTRL.WSFLASH.

⁴⁾ Programming and erase times depend on the internal Flash clock source. The control state machine needs a few system clock cycles. This increases the stated durations noticably only at extremely low system clock frequencies.

Electrical Parameters

4.7.2 Definition of Internal Timing

The internal operation of the XC223[04]L is controlled by the internal system clock $f_{\rm SYS}$. Because the system clock signal $f_{\rm SYS}$ can be generated from a number of internal and external sources using different mechanisms, the duration of the system clock periods (TCSs) and their variation (as well as the derived external timing) depend on the mechanism used to generate $f_{\rm SYS}$. This must be considered when calculating the timing for the XC223[04]L.

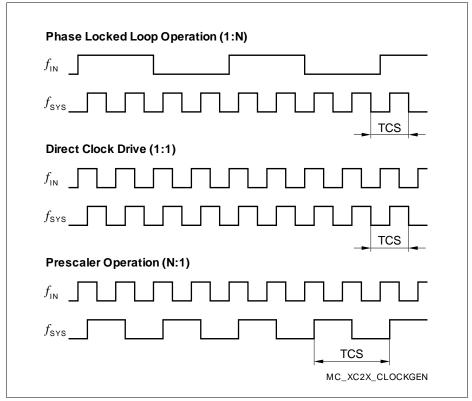


Figure 18 Generation Mechanisms for the System Clock

Note: The example of PLL operation shown in Figure 18 uses a PLL factor of 1:4; the example of prescaler operation uses a divider factor of 2:1.

The specification of the external timing (AC Characteristics) depends on the period of the system clock (TCS).



Electrical Parameters

The timing in the AC Characteristics refers to TCSs. Timing must be calculated using the minimum TCS possible under the given circumstances.

The actual minimum value for TCS depends on the jitter of the PLL. Because the PLL is constantly adjusting its output frequency to correspond to the input frequency (from crystal or oscillator), the accumulated jitter is limited. This means that the relative deviation for periods of more than one TCS is lower than for a single TCS (see formulas and Figure 19).

This is especially important for bus cycles using waitstates and for the operation of timers, serial interfaces, etc. For all slower operations and longer periods (e.g. pulse train generation or measurement, lower baudrates, etc.) the deviation caused by the PLL jitter is negligible.

The value of the accumulated PLL jitter depends on the number of consecutive VCO output cycles within the respective timeframe. The VCO output clock is divided by the output prescaler K2 to generate the system clock signal $f_{\rm SYS}$. The number of VCO cycles is K2 × **T**, where **T** is the number of consecutive $f_{\rm SYS}$ cycles (TCS).

The maximum accumulated jitter (long-term jitter) D_{Tmax} is defined by:

$$D_{Tmax}$$
 [ns] = ±(220 / (K2 × f_{SYS}) + 4.3)

This maximum value is applicable, if either the number of clock cycles T > $(f_{SYS} / 1.2)$ or the prescaler value K2 > 17.

In all other cases for a timeframe of $\mathbf{T} \times TCS$ the accumulated jitter D_T is determined by:

$$\mathbf{D_{T}} \, [\mathbf{ns}] = \mathbf{D_{Tmax}} \times [(1 \text{ - } 0.058 \times \text{K2}) \times (\text{T - 1}) \, / \, (0.83 \times f_{\text{SYS}} \text{ - 1}) + 0.058 \times \text{K2}]$$

 $f_{\rm SYS}$ in [MHz] in all formulas.

Example, for a period of 3 TCSs @ 33 MHz and K2 = 4:

 $D_{max} = \pm (220 / (4 \times 33) + 4.3) = 5.97$ ns (Not applicable directly in this case!)

$$D_3 = 5.97 \times [(1 - 0.058 \times 4) \times (3 - 1) \, / \, (0.83 \times 33 - 1) + 0.058 \times 4]$$

$$= 5.97 \times [0.768 \times 2 \, / \, 26.39 \, + \, 0.232]$$

= 1.7 ns

Example, for a period of 3 TCSs @ 33 MHz and K2 = 2:

 $D_{\text{max}} = \pm (220 / (2 \times 33) + 4.3) = 7.63 \text{ ns (Not applicable directly in this case!)}$

$$D_3 = 7.63 \times [(1 - 0.058 \times 2) \times (3 - 1) / (0.83 \times 33 - 1) + 0.058 \times 2]$$

$$= 7.63 \times [0.884 \times 2 / 26.39 + 0.116]$$

= 1.4 ns



Electrical Parameters

Table 30 Standard Pad Parameters for Upper Voltage Range (cont'd)

Parameter	Symbol		Values		Unit	Note /
		Min.	Тур.	Max.		Test Condition
Rise and Fall times (10% - 90%)	t _{RF} CC	_	_	38 + 0.6 x C _L	ns	$C_{L} \ge 20 \text{ pF};$ $C_{L} \le 100 \text{ pF};$ Driver_Strength = Medium
		_	_	1 + 0.45 x C _L	ns	$C_L \ge 20 \text{ pF};$ $C_L \le 100 \text{ pF};$ Driver_Strength = Strong; Driver_Edge= Soft
		_	_	16 + 0.45 x C_{L}	ns	$C_{L} \ge 20 \text{ pF};$ $C_{L} \le 100 \text{ pF};$ Driver_Strength = Strong; Driver_Edge= Slow
		_	_	200 + 2.5 x C _L	ns	$C_L \ge 20 \text{ pF};$ $C_L \le 100 \text{ pF};$ Driver_Strength = Weak

The total output current that may be drawn at a given time must be limited to protect the supply rails from damage. For any group of 16 neighboring output pins, the total output current in each direction (ΣI_{OL} and Σ-I_{OH}) must remain below 25 mA.

Table 31 Standard Pad Parameters for Lower Voltage Range

				•	•	
Parameter	Symbol	Values			Unit	Note /
		Min.	Тур.	Max.		Test Condition
Maximum output driver current (absolute value) ¹⁾	I _{Omax} CC	_	_	1.8	mA	Driver_Strength = Medium
		_	-	3.0	mA	Driver_Strength = Strong
		_	_	0.3	mA	Driver_Strength = Weak



Electrical Parameters

4.7.5 Synchronous Serial Interface Timing

The following parameters are applicable for a USIC channel operated in SSC mode.

Note: These parameters are not subject to production test but verified by design and/or characterization.

Note: Operating Conditions apply.

Table 32 is valid under the following conditions: C_L = 20 pF; SSC= master; voltage_range= upper

Table 32 USIC SSC Master Mode Timing for Upper Voltage Range

Parameter	Symbol	Values			Unit	Note /
		Min.	Тур.	Max.	1	Test Condition
Slave select output SELO active to first SCLKOUT transmit edge	t ₁ CC	<i>t</i> _{SYS} - 8 ¹⁾	_	_	ns	
Slave select output SELO inactive after last SCLKOUT receive edge	t ₂ CC	<i>t</i> _{SYS} - 6 ¹⁾	_	-	ns	
Data output DOUT valid time	t ₃ CC	-6	_	9	ns	
Receive data input setup time to SCLKOUT receive edge	t ₄ SR	31	_	_	ns	
Data input DX0 hold time from SCLKOUT receive edge	t ₅ SR	-4	_	_	ns	

¹⁾ $t_{SYS} = 1 / f_{SYS}$



Electrical Parameters

Table 33 is valid under the following conditions: C_L = 20 pF; SSC= master; voltage_range= lower

Table 33 USIC SSC Master Mode Timing for Lower Voltage Range

Parameter	Symbol	Values			Unit	Note /
		Min.	Тур.	Max.		Test Condition
Slave select output SELO active to first SCLKOUT transmit edge	t ₁ CC	<i>t</i> _{SYS} - 10 ¹⁾	-	-	ns	
Slave select output SELO inactive after last SCLKOUT receive edge	t ₂ CC	t _{SYS} - 9 ¹⁾	-	-	ns	
Data output DOUT valid time	t ₃ CC	-7	-	11	ns	
Receive data input setup time to SCLKOUT receive edge	t ₄ SR	40	-	-	ns	
Data input DX0 hold time from SCLKOUT receive edge	t ₅ SR	-5	-	-	ns	

¹⁾ $t_{SYS} = 1 / f_{SYS}$

Table 34 is valid under the following conditions: C_L = 20 pF; SSC= slave; voltage_range= upper

Table 34 USIC SSC Slave Mode Timing for Upper Voltage Range

Parameter	Symbol	Values			Unit	Note /
		Min.	Тур.	Max.		Test Condition
Select input DX2 setup to first clock input DX1 transmit edge ¹⁾	<i>t</i> ₁₀ SR	10	-	-	ns	
Select input DX2 hold after last clock input DX1 receive edge ¹⁾	<i>t</i> ₁₁ SR	7	-	-	ns	
Receive data input setup time to shift clock receive edge ¹⁾	<i>t</i> ₁₂ SR	7	-	-	ns	

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Electrical Parameters

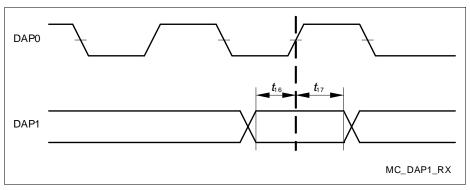


Figure 23 DAP Timing Host to Device

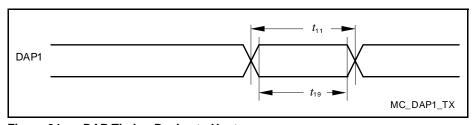


Figure 24 DAP Timing Device to Host

Note: The transmission timing is determined by the receiving debugger by evaluating the sync-request synchronization pattern telegram.

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Package and Reliability

particular, the size of the Exposed Pad (if present) may vary.

If different device types are considered or planned for an application, it must be ensured that the board layout fits all packages under consideration.

Package Outlines

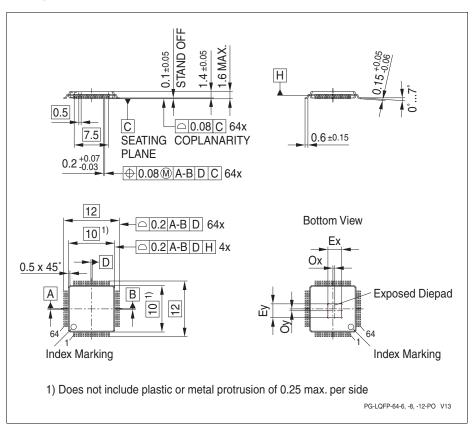


Figure 27 PG-LQFP-64-22/-24 (Plastic Green Thin Quad Flat Package)

All dimensions in mm.

You can find complete information about Infineon packages, packing and marking in our Infineon Internet Page "Packages": http://www.infineon.com/packages

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